TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM3K04FU

## **High Speed Switch Applications**

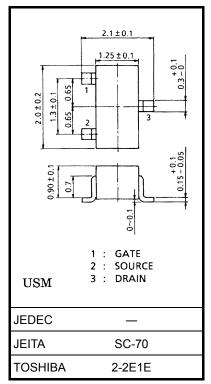
Unit: mm

- With built-in gate-source resistor:  $RGS = 1 M\Omega$  (typ.)
- 2.5 V gate drive
- Low gate threshold voltage:  $V_{th} = 0.7 \sim 1.3 \text{ V}$
- Small package

## **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	$V_{DS}$	20	V	
Gate-source voltage	V <sub>GSS</sub>	10	V	
DC drain current	ID	100	mA	
Drain power dissipation	P <sub>D</sub>	100	mW	
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature range	T <sub>stg</sub>	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



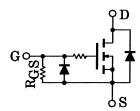
Weight: 0.006 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Marking



## **Equivalent Circuit**



# **Electrical Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, V_{DS} = 0$	_	_	15	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	nt	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0$	_	_	1	μА
Gate threshold vol	tage	$V_{th}$	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.7	_	1.3	V
Forward transfer a	dmittance	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$	25	50	_	mS
Drain-source ON resistance		R <sub>DS</sub> (ON)	$I_D$ = 10 mA, $V_{GS}$ = 2.5 V	_	4	12	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	11.0	_	pF
Reverse transfer of	apacitance	C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.3	_	pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	9.3	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$	_	0.16	_	μS
	Turn-off time	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$	_	0.19	_	
Gate-source resistor		R <sub>GS</sub>	V <sub>GS</sub> = 0~10 V	0.7	1.0	1.3	ΜΩ

# **Switching Time Test Circuit**

Test circuit

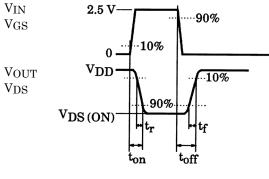
2.5 V  $10 \mu s$  $v_{IN}$ 

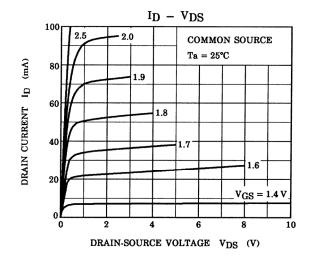
 $\begin{array}{c|c} \underline{I_D} & OUT & V_{DD} = 3 \text{ V} \\ \hline & D.U. \leq 1\% \end{array}$  $V_{IN}: t_r, t_f < 5 \text{ ns}$  $(Z_{out} = 50 \Omega)$ COMMON SOURCE  $Ta = 25^{\circ}C$ 

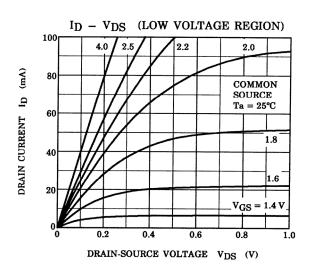
(b)  $V_{IN}$  $V_{\rm GS}$ 

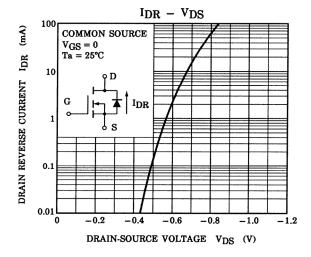
 $V_{\rm DS}$ 

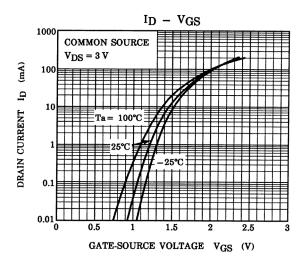
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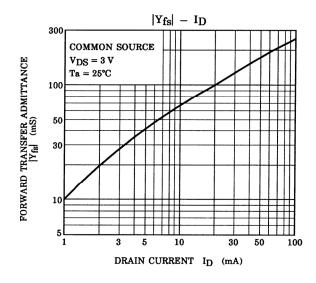


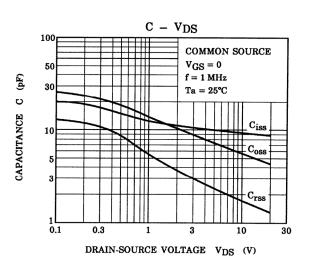


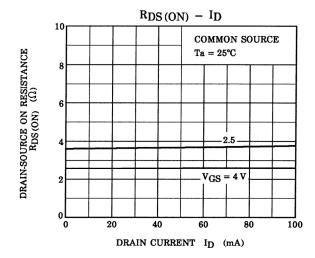


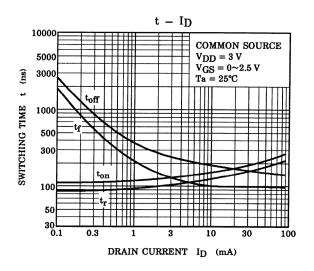


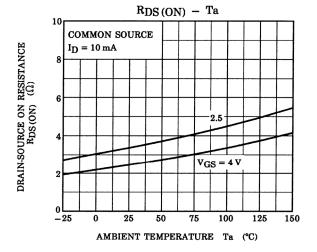


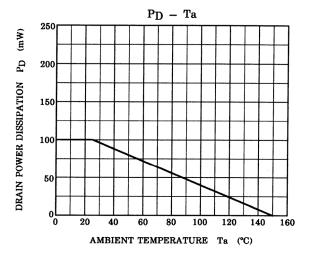












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20070701-EN GENERAL

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